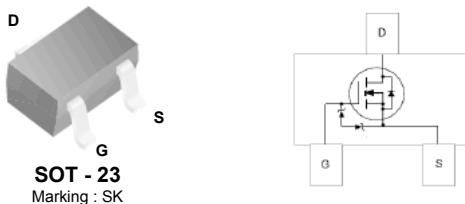


## BSS138K

### N-Channel Logic Level Enhancement Mode Field Effect Transistor

#### Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Pb Free/RoHS Compliant
- Green Compound
- ESD HBM=2000V as per JEDEC A114A ; ESD CDM = 2000V as per JEDEC C101C



#### Absolute Maximum Ratings \* $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{DSS}$	Drain-Source Voltage	50	V
$V_{GSS}$	Gate-Source Voltage	$\pm 12$	V
$I_D$	Drain Current Continuous Pulsed	0.22 0.88	A
$T_J$	Operating Junction Temperature Range	-55 to +150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to +150	$^\circ\text{C}$

\* These ratings are limiting values above which the serviceability of any semiconductor device maybe impaired.

#### Thermal Characteristics

Symbol	Parameter	Value	Units
$P_D$	Total Device Dissipation Derating above $T_A = 25^\circ\text{C}$	350 2.8	mW mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient *	350	$^\circ\text{C}/\text{W}$

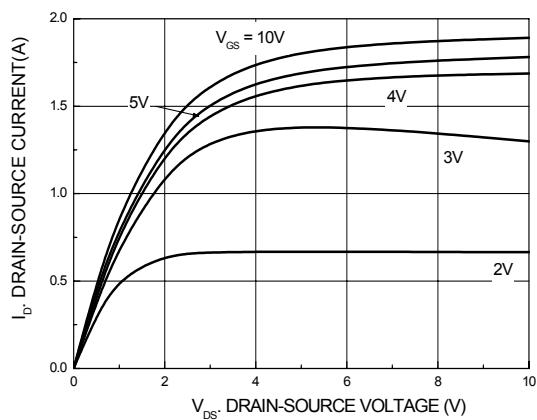
\* Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch. Minimum land pad size

**Electrical Characteristics**  $T_A = 25^\circ\text{C}$  unless otherwise noted

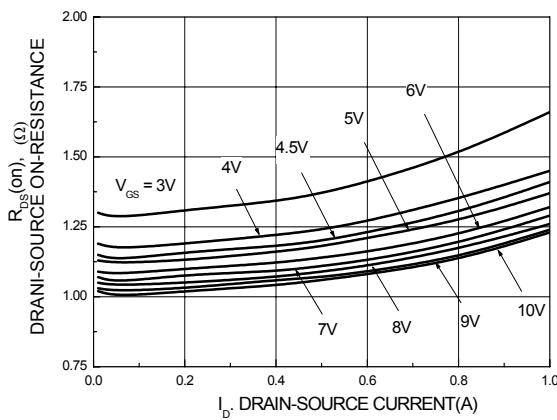
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}$ , $I_D = 10\mu\text{A}$	50			V
$\frac{BV_{DSS}}{T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , Referenced to $25^\circ\text{C}$		0.11		$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 50\text{V}$ , $V_{GS} = 0\text{V}$			0.1	$\mu\text{A}$
$I_{GSS}$	Gate-Body Leakage	$V_{GS} = \pm 12\text{V}$ , $V_{DS} = 0\text{V}$ $V_{GS} = \pm 10\text{V}$ , $V_{DS} = 0\text{V}$ $V_{GS} = \pm 5\text{V}$ , $V_{DS} = 0\text{V}$			$\pm 1$ $\pm 0.5$ $\pm 0.05$	$\mu\text{A}$
<b>On Characteristics</b>						
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 250\mu\text{A}$	0.6		1.2	V
$\frac{V_{GS(\text{th})}}{T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 1\text{mA}$ , Referenced to $25^\circ\text{C}$		-1.4		$\text{mV}/^\circ\text{C}$
$R_{DS(\text{ON})}$	Static Drain-Source On-Resistance	$V_{GS} = 1.8\text{V}$ , $I_D = 50\text{mA}$ , $V_{GS} = 2.5\text{V}$ , $I_D = 50\text{mA}$ , $V_{GS} = 5\text{V}$ , $I_D = 50\text{mA}$ ,			2.5 2.0 1.6	$\Omega$
$I_{D(\text{ON})}$	On-State Drain Current	$V_{GS} = 10\text{V}$ , $V_{DS} = 5\text{V}$	0.2			A
$g_F$	Forward Transconductance	$V_{DS} = 10\text{V}$ , $I_D = 200\text{mA}$	200			$\text{mS}$
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{V}$ , $V_{GS} = 0\text{V}$ , $f = 1.0\text{MHz}$		58		$\text{pF}$
$C_{oss}$	Output Capacitance			9.75		
$C_{rss}$	Reverse Transfer Capacitance			5.2		
$R_G$	Gate Resistance	$V_{DS} = 5\text{V}$ , $V_{GS} = 10\text{mV}$		281		$\Omega$
<b>Switching Characteristics</b>						
$t_{D(\text{ON})}$	Turn-On Delay Time	$V_{DD} = 30\text{V}$ , $I_D = 0.29\text{A}$ , $V_{GS} = 10\text{V}$ , $R_{\text{GEN}} = 6\Omega$		5	ns	
$t_r$	Turn-On Rise Time			5		
$t_{D(\text{OFF})}$	Turn-Off Delay Time			60		
$t_f$	Turn-Off Fall Time			35		
$Q_g$	Total Gate Change	$V_{DS} = 25\text{V}$ , $I_D = 0.2\text{A}$ , $V_{GS} = 10\text{V}$ , $I_G = 0.1\text{mA}$		2.4	nC	
$Q_{gs}$	Gate-Source Change			0.5		
$Q_{gd}$	Gate-Drain Change			0.5		
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$V_{sd}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{V}$ , $I_S = 115\text{mA}$			1.2	V

## Typical Performance Characteristics

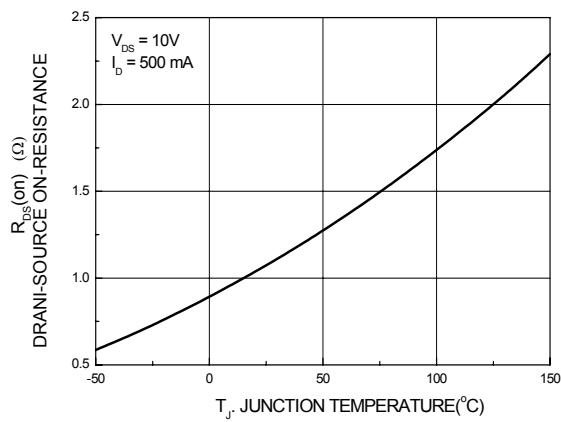
**Figure 1. On-Region Characteristics**



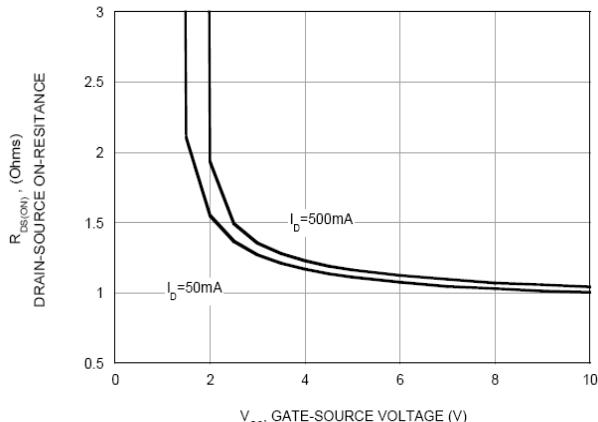
**Figure 2. On-Resistance Variation with Gate Voltage and Drain Current**



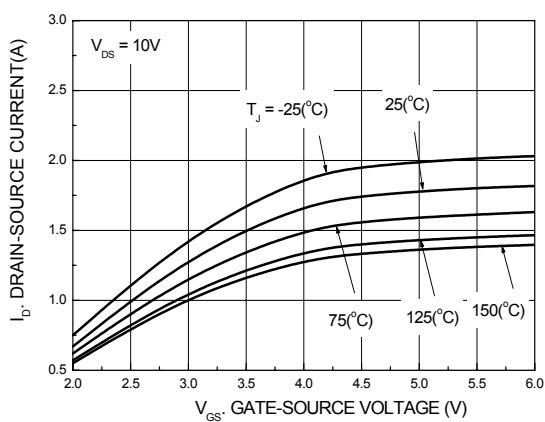
**Figure 3. On-Resistance Variation with Temperature**



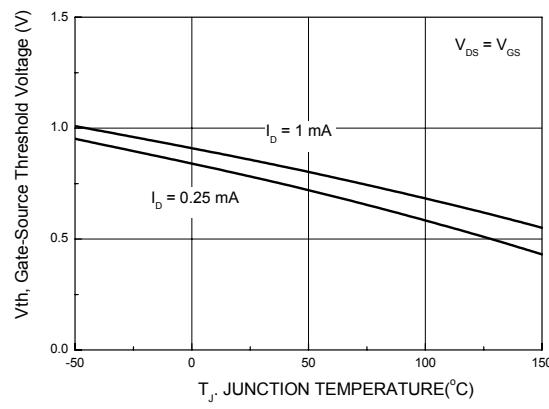
**Figure 4. On-Resistance Variation with Gate-Source Voltage**



**Figure 5. Transfer Characteristics**

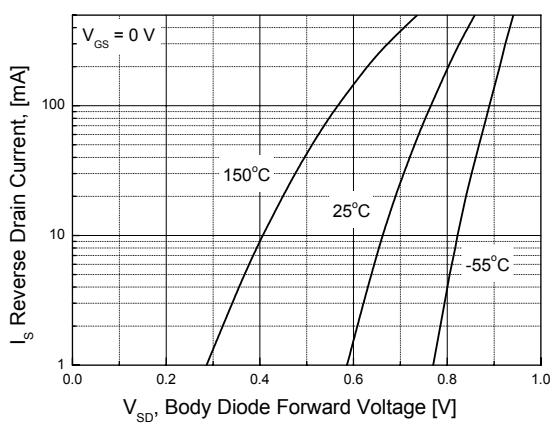


**Figure 6. Gate Threshold Variation with Temperature**



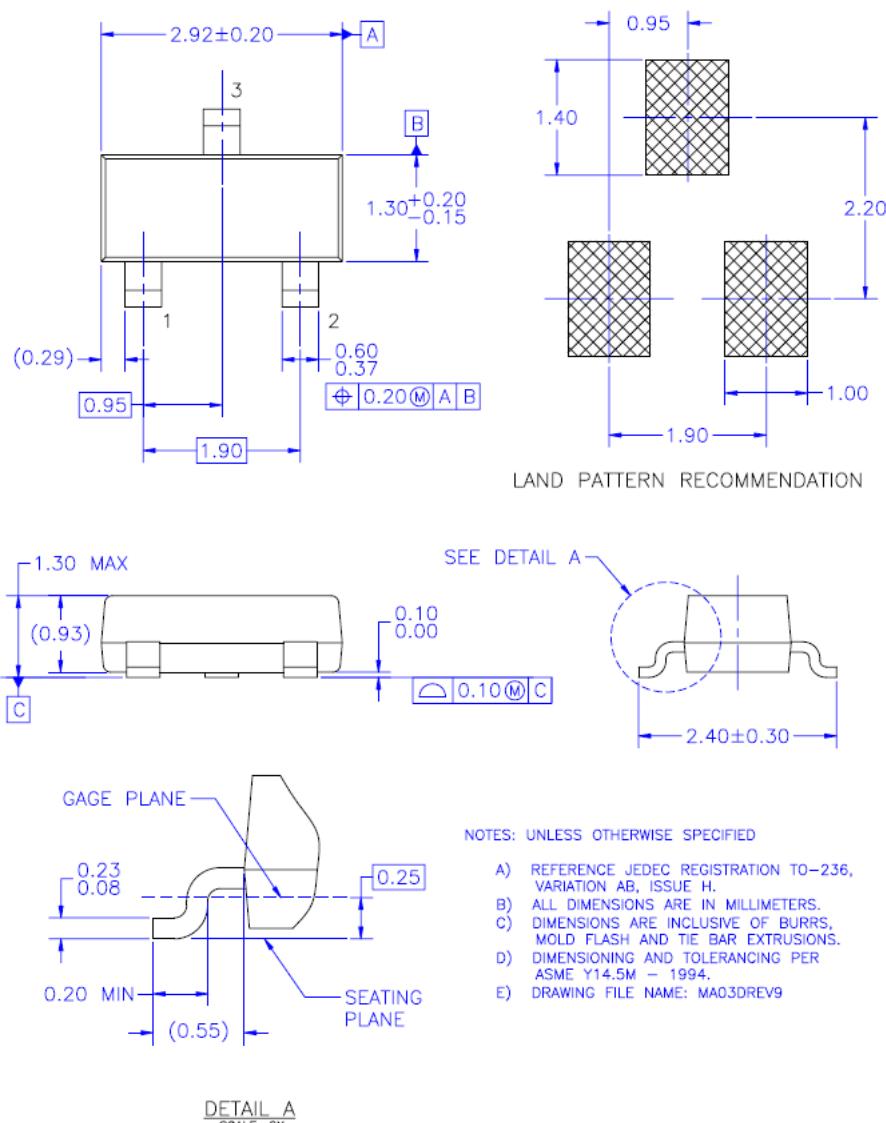
## Typical Performance Characteristics (Continue)

**Figure 7. Reverse Drain Current Variation with Diode Forward Voltage and Temperature**



## Physical Dimensions

### SOT - 23





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